

Device Modeling Report

COMPONENTS:
DIODE/ GENERAL PURPOSE RECTIFIER / STANDARD
PART NUMBER: RHRG7560
MANUFACTURER: INTERSIL
REMARK: TC=110C

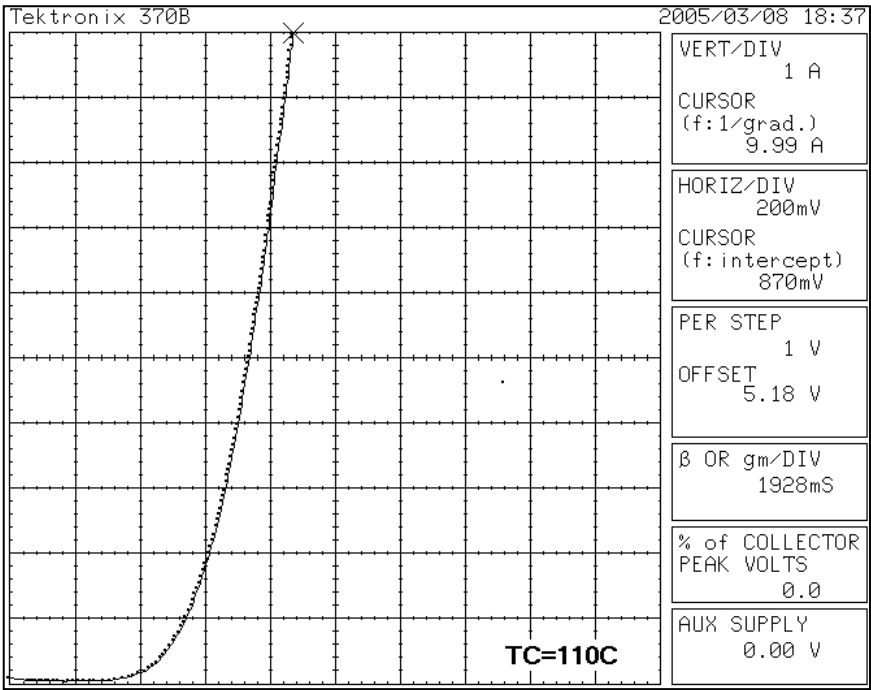


Bee Technologies Inc.

PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

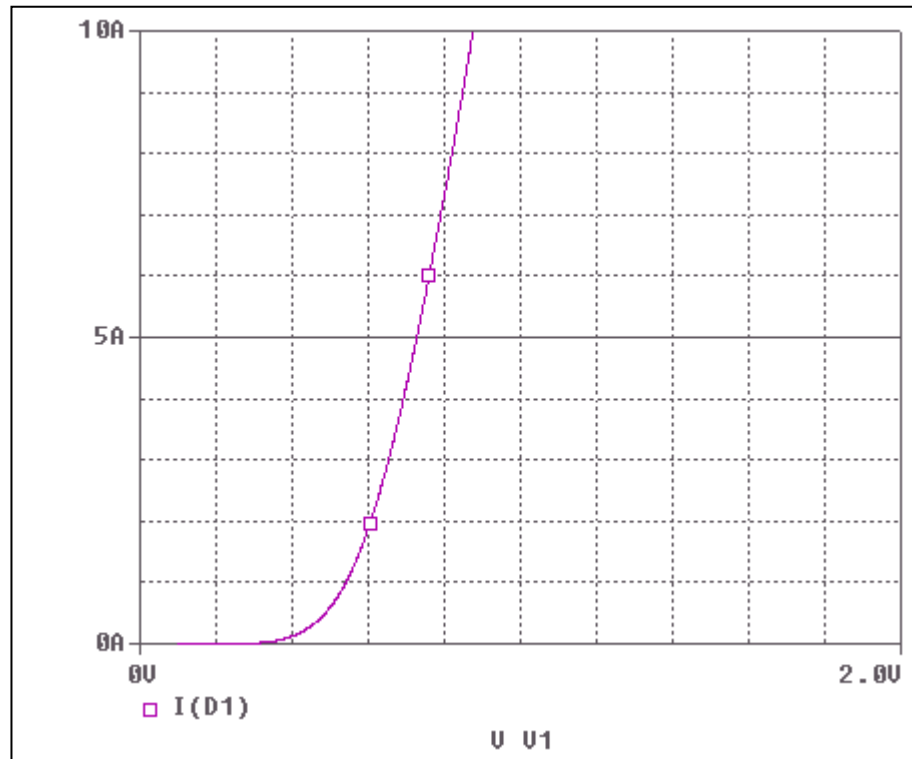
Forward Current Characteristic

Reference

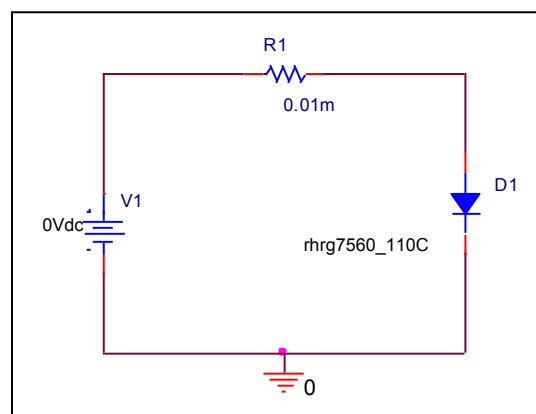


Forward Current Characteristic

Circuit Simulation Result

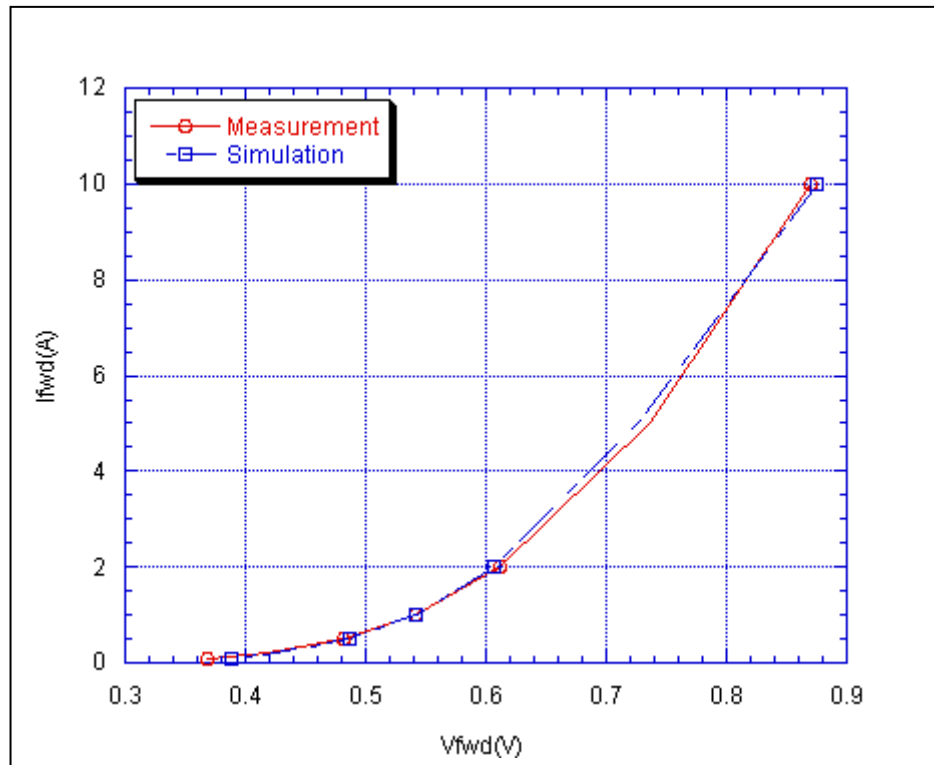


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

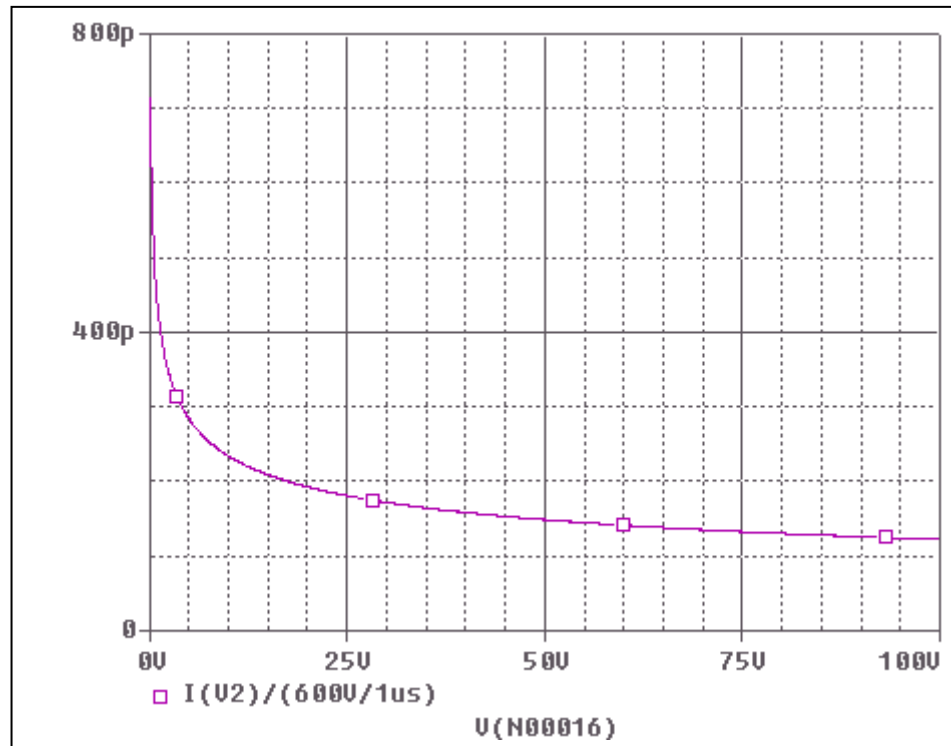


Simulation Result

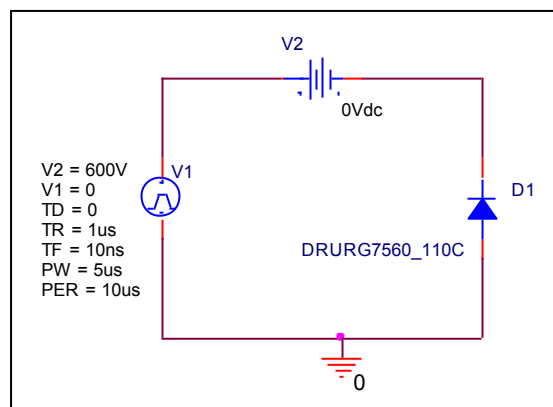
I_{fwd} (A)	V_{fwd} (V) Measurement	V_{fwd} (V) Simulation	%Error
0.1	0.368	0.388	5.4347
0.2	0.418	0.4258	1.8660
0.5	0.482	0.4867	0.9751
1	0.542	0.5412	-0.1476
2	0.612	0.6063	-0.9313
5	0.736	0.7266	-1.2771
10	0.87	0.8754	0.6206

Capacitance Characteristic

Circuit Simulation Result

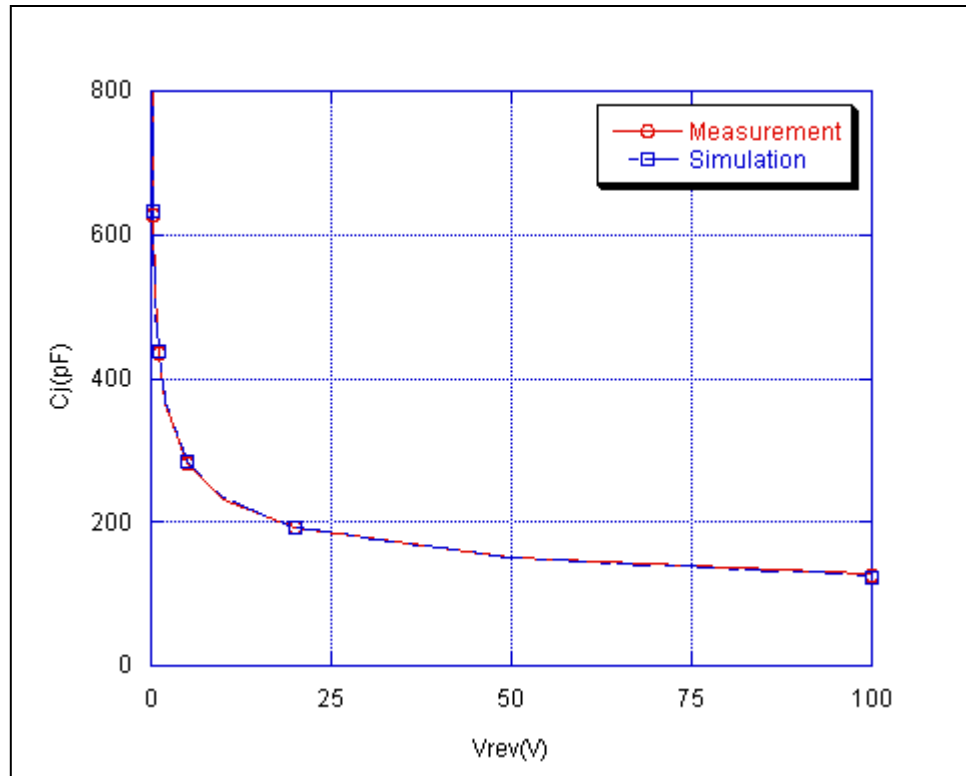


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

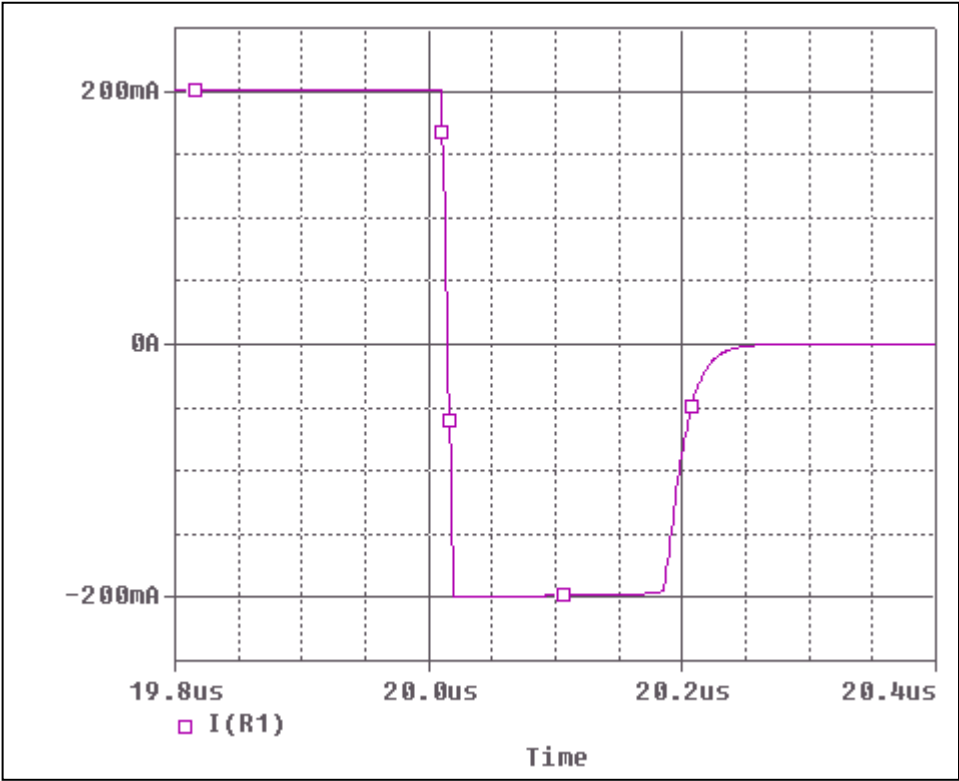


Simulation Result

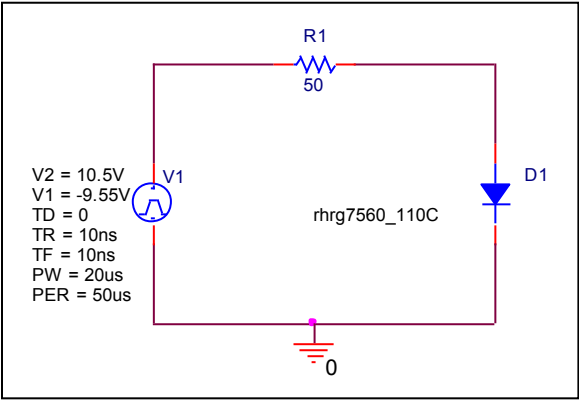
Vrev(V)	Cj(pF) Measurement	Cj(pF) Simulation	%Error
0	827.110	827.110	0.00
0.2	627.100	633.835	-1.07
0.5	517.330	519.817	-0.48
1	435.220	438.373	-0.72
2	364.100	364.814	-0.20
5	281.200	284.275	-1.09
10	232.302	234.130	-0.79
20	193.311	193.000	0.16
50	151.302	150.000	0.86
100	126.350	122.350	3.17

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

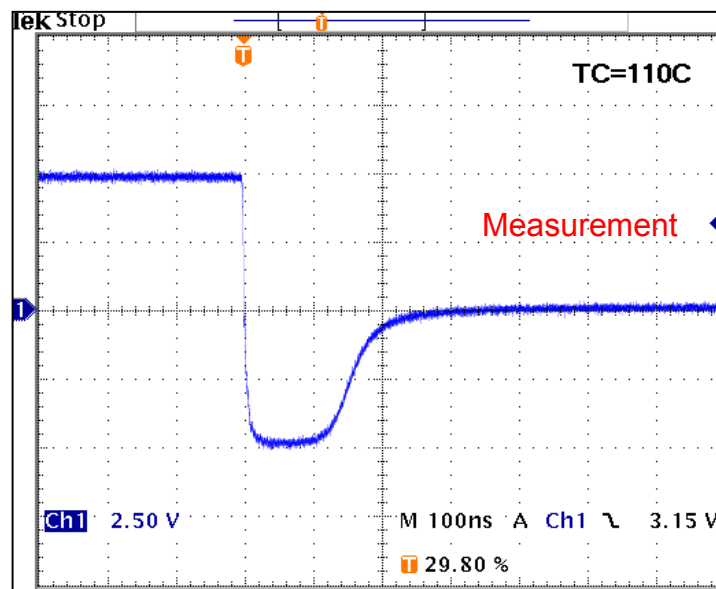


Compare Measurement vs. Simulation

trr	Measurement		Simulation		%Error
	202	ns	203	ns	

Reverse Recovery Characteristic

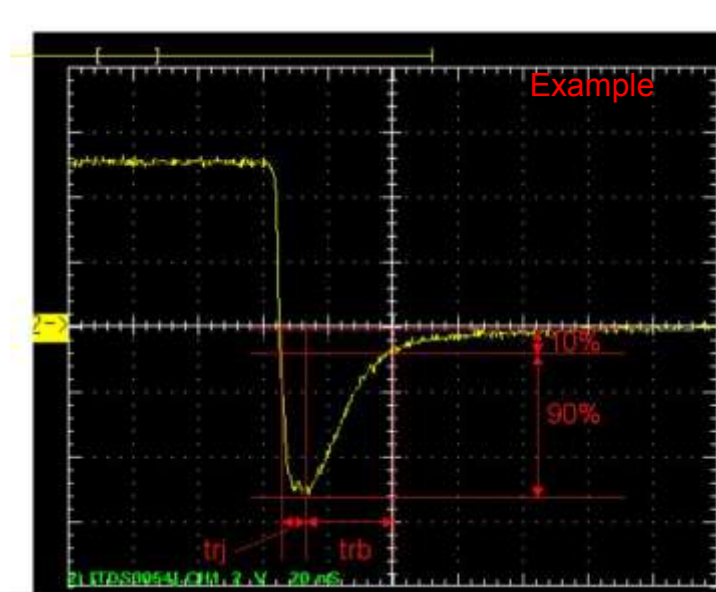
Reference



$T_{rj} = 74 \text{ (ns)}$

$T_{rb} = 128 \text{ (ns)}$

Conditions: $I_{fwd} = I_{rev} = 0.2 \text{ (A)}$, $R_I = 50$



Relation between t_{rj} and t_{rb}